

L Number	Hits	Search Text	DB	Time stamp
2	2	@ad<=20000203 and 'n' adjl 'electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 09:57
3	6	@ad<=20000203 and 'LED'and 'n electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:15
4	1	@ad<=20000203 and 'LED' and 'n electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:13
5	2	@ad<=20000203 and 'n electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:17
6	2	@ad<=20000203 and 'ITO' with 'n-electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:17
7	9	@ad<=20000203 and 'transparent' with 'n-electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:18
188	3	@ad<=20000203 and 'gallium compound' and 'n electrode' and 'p electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:33
189	1207	@ad<=20000203 and (257/98).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 12:23
190	661	@ad<=20000203 and (257/94).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:38
191	444	@ad<=20000203 and (257/96).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:38
192	326	@ad<=20000203 and (257/97).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:38
193	936	@ad<=20000203 and (257/103).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:39
194	326	@ad<=20000203 and (257/13).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:40
195	235	@ad<=20000203 and (257/15).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:40

196	341	@ad<=20000203 and (257/22).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:40
198	3	@ad<=20000203 and 'n-electrode' same 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:00
200	152	@ad<=20000203 and 'LED' same 'ITO' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:11
202	4	@ad<=20000203 and 'gallium nitride' same 'ITO' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:02
203	48	@ad<=20000203 and 'LED' with 'ITO' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:16
204	1	@ad<=20000203 and 'nitride semiconductor' with 'ITO' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:16
205	49	@ad<=20000203 and 'nitride semiconductor' and 'ITO' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:38
206	47	@ad<=20000203 and 'n' near2 'electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:38
207	13	@ad<=20000203 and 'n' near1 'electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 10:38
208	1323	@ad<=20000203 and (257/99).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 12:24
-	507	(257/21).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 09:18
-	16	((257/21).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	107	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 13:32
-	1	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode' with 'pad'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 07:36

-	2	("6172382").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:44
-	16	((257/21).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 16:46
-	273	@ad<=20000203 and 'GaN' and 'electrode' with 'transparent'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:26
-	3	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode' with 'transparent'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 09:56
-	0	@ad<=20000203 and 'GaN' and 'n-type electrode' with 'trans'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:01
-	2	@ad<=20000203 and 'GaN' and 'n-type electrode' with 'transmissive'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:01
-	7	@ad<=20000203 and 'GaN' and 'transmissive electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:06
-	996	(257/59).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	0	("103 and 'GaN'").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:14
-	6	((257/59).CCLS.) and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:23
-	837	(257/72).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	2	((257/72).CCLS.) and 'GaN' and 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:24
-	166	@ad<=20000203 and 'GaN' and 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/23 11:27
-	115	@ad<=20000203 and 'GaN' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:11

-	16	((257/21).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:53
-	1128	(257/59).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:54
-	957	(257/72).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:54
-	560	(438/22).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 11:05
-	1108	((438/22) or (257/79)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 11:07
-	106	@ad<=20000203 and 'GaN' and 'n-type' and 'p-type' and 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 12:03
-	35	@ad<=20000203 and 'GaN' and 'n-type' same 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:48
-	7979	((257/13-15) or (257/79-103)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:48
-	463	((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:03
-	709	(438/22-24).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 13:50
-	0	@ad<=20000203 and 'light emitting diode' and 'n-type electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:58
-	244	@ad<=20000203 and 'light emitting diode' and 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:47
-	13	(@ad<=20000203 and 'light emitting diode' and 'n-type electrode') and ITO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:48
-	0	@ad<=20000203 and 'n-type electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:58

-	0	@ad<=20000203 and 'n-type electrode' near 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 15:59
-	55	@ad<=20000203 and 'n-type electrode' and 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:03
-	1	@ad<=20000203 and 'n-type electrode' and 'TCO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:05
-	49	@ad<=20000203 and 'LED' and 'transmissive electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:06
-	8	@ad<=20000203 and 'GaN' and 'transmissive electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 16:07
-	1197	@ad<=20000203 and (257/98).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:36
-	145	@ad<=20000203 and (257/91).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:52
-	655	@ad<=20000203 and (257/94).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:53
-	925	@ad<=20000203 and (257/103).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:53
-	1315	@ad<=20000203 and (257/99).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:54
-	2	("6100545").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 09:54
-	7	@ad<=20000203 and 'GaN' with 'transparent' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:56
-	22	@ad<=20000203 and 'GaN' and 'transparent' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:29
-	8	@ad<=20000203 and 'GaN' and 'transparent' same 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:39

-	24	@ad<=20000203 and 'GaN' with 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:40
-	16	@ad<=20000203 and 'Gallium nitride' with 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:40
-	26	@ad<=20000203 and 'GaN' and 'n-type' with 'p-type' same 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:57
-	0	@ad<=20000203 and 'GaN' and 'n-type transparent electrode' same 'p-type transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:58
-	0	@ad<=20000203 and 'n-type transparent electrode' same 'p-type transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 13:59
-	486	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:11
-	314	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'gallium nitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:04
-	2	"20010042860"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 13:01
-	496	(((257/13-15) or (257/79-103)).CCLS.) and @ad<=20000203 and 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:12
-	112	@ad<=20000203 and 'GaN' and 'n-type electrode' same 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:14
-	46	@ad<=20000203 and 'GaN' and 'n-type electrode' same 'thickness'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:24
-	3	@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:26
-	2	(@ad<=20000203 and 'GaN' and 'thin' with 'n-type electrode') and thickness near3 (nm nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:28
-	25	@ad<=20000203 and 'GaN' and electrode near3 thickness near3 (nm nanometer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:39

-	1	@ad<=20000203 and 'GaN' and electrode near3 thickness near3 '30'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:33
-	40	@ad<=20000203 and 'GaN' same 'transparent electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:35
-	2	@ad<=20000203 and 'GaN' same 'transparent' with 'n type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:36
-	116	@ad<=20000203 and 'GaN' and 'n' with 'electrode' same '50'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:40
-	33	@ad<=20000203 and 'GaN' and 'n' near2 'electrode' with '50'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:40
-	10	@ad<=20000203 and 'GaN' and 'n' near2 'electrode' with '50 nm'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 07:33
-	19	@ad<=20000203 and 'GaN' and 'n' with 'electrode' with '50 nm'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:47
-	10	@ad<=20000203 and 'GaN' and 'n' adj2 'electrode' with '50 nm'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:48
-	2	'reflective index' same 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 13:10
-	0	'reflective index of GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 13:08
-	380	'refractive index' same 'GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 06:01
-	0	'refractive index of GaN'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 13:10
-	199	'GaN' with 'refractive index'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 13:19
-	283	@ad<=20000103 and 'sapphire' with 'refractive index'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 13:25

-	6040	@ad<=20000103 and 'air' with 'refractive index'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 13:29
-	103	@ad<=20000203 and 'GaN' with 'substrate' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:57
-	18	@ad<=20000203 and 'GaN' adj1 'substrate' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 13:54
-	82	@ad<=20000203 and 'GaN' same 'sapphire' same 'substrate' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 15:57
-	78	@ad<=20000203 and 'substrate' same 'GaN' with 'sapphire' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/28 16:01
-	78	@ad<=20000203 and 'substrate' with 'GaN' with 'sapphire' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 06:07
-	854	@ad<=20000203 and 'refractive index' with 'GaAs'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 06:03
-	18	@ad<=20000203 and 'GaN substrate' and 'n-type electrode' and 'p-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:32
-	2	@ad<=20000203 and 'GaN' and 'n-type electrode' with 'pad'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 07:34
-	1	@ad<=20000203 and 'GaN substrate' and 'thin' with 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 07:36
-	12	@ad<=20000203 and 'n-type electrode' and 'p-type electrode' and 'pad electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 07:37
-	0	@ad<=20000203 and 'GaN substrate' and 'ITO' with 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 08:23
-	0	@ad<=20000203 and 'GaN' and 'ITO' with 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 08:23
-	124	@ad<=20000203 and 'GaN' and 'ITO' with 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 08:33

-	0	@ad<=20000203 and 'GaN' and 'ITO' with 'n' adj1 'electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 08:34
-	61	@ad<=20000203 and 'transparent' same 'n-type electrode'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 08:45
-	0	@ad<=20000203 and 'n-type electrode' with 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 08:46
-	2	@ad<=20000203 and 'n-type electrode' same 'indium tin oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/29 08:46
-	2	@ad<=20000203 and 'n-type electrode' same 'ITO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/01 08:06
-	2	"20010042860"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 09:21
-	0	JP10-163531	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 09:22
-	2	'JP 10163531'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 09:24
-	83	yamada-motokazu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 09:25
-	34	yamada-motokazu.in. and 'LED'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/30 09:25